

Appl. No. 10/050,348

**Amendments to the Claims**

Claims 1-40 (Cancelled).

41. (Previously presented) A transistor structure, comprising:  
a gate oxide layer over a semiconductive substrate, the gate oxide layer comprising silicon dioxide and having a thickness of about 5Å; the gate oxide layer having a nitrogen-enriched region which is only in an upper half of the gate oxide layer;  
at least one conductive layer over the gate oxide layer; and  
source/drain regions within the semiconductive substrate; the source/drain regions being gatedly connected to one another by the conductive layer.

42. (Original) The structure of claim 41 wherein the conductive layer comprises conductively-doped silicon.

43. (Original) The structure of claim 41 wherein the conductive layer comprises p-type conductively-doped silicon.

Claims 44-47 (Cancelled).